

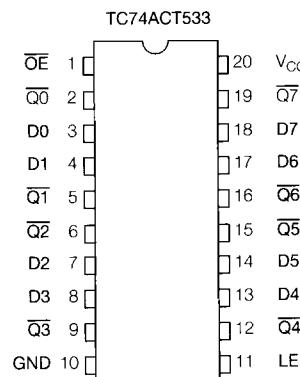
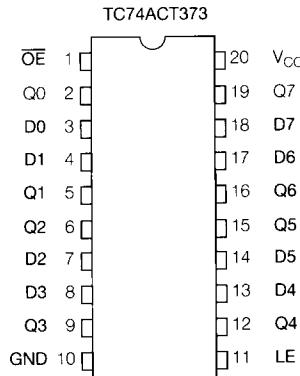
TC74ACT373, 533 Octal D-Type Latch with 3-State Output

373: Non-Inverting,
533: Inverting

Features:

- High Speed:** $t_{pd} = 5.2\text{ns}$ (typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation:** $I_{CC} = 8\mu\text{A}$ (max.) at $T_a = 25^\circ\text{C}$
- Compatible with TTL Outputs:** $V_{IL} = 0.8\text{V}$ (max.); $V_{IH} = 2.0\text{V}$ (min.)
- Symmetrical Output Impedance:** $|I_{OH}| = |I_{OL}| = 24\text{mA}$ (min.). Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays:** $t_{pLH} = t_{pHL}$
- Pin and Function Compatible with 74F373/533**
- ACT373 Available in DIP, SOIC, SOP and SSOP Packages**
- ACT368 Available in DIP, SOIC and SOP Packages**

Pin Assignment



The TC74ACT373 and TC74ACT533 are advanced high speed CMOS OCTAL LATCHES with 3-STATE OUTPUT fabricated with silicon gate and double-layer metal wiring C²MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL, while maintaining the CMOS low power dissipation.

These devices may be used as a level converter for interfacing TTL or NMOS to high speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input (OE).

When the OE input is high, the eight outputs are in a high impedance state.

The TC74ACT373 has non-inverting outputs, and TC74ACT533 has inverting outputs.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Truth Table

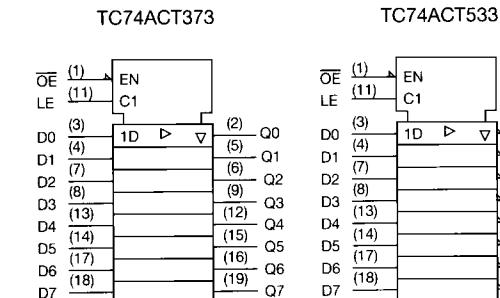
INPUTS			OUTPUTS	
OE	LE	D	Q(373)	Q̄(533)
H	X	X	Z	Z
L	L	X	Q _n	Q̄ _n
L	H	L	L	H
L	H	H	H	L

X: Don't care

Z: High Impedance

Q_n (Q̄_n): Q (Q̄) outputs are latched at the time when the LE input is taken to a low logic level.

IEC Logic Symbol



Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	-0.5~ V_{CC} + 0.5	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 200	mA
Power Dissipation	P_D	500 (DIP) /180 (SOP)	mW
Storage Temperature	T_{STG}	-65~150	°C
Lead Temperature 1sec	T_L	300	°C

* 500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$.
From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of
 $-10\text{mW}/^{\circ}\text{C}$ should be applied up to 300mW.

Recommended Operating Conditions

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	4.5~5.5	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{OPR}	-40~85	°C
Input Rise and Fall Time	$t_{R/F}$	0~10	ns/v

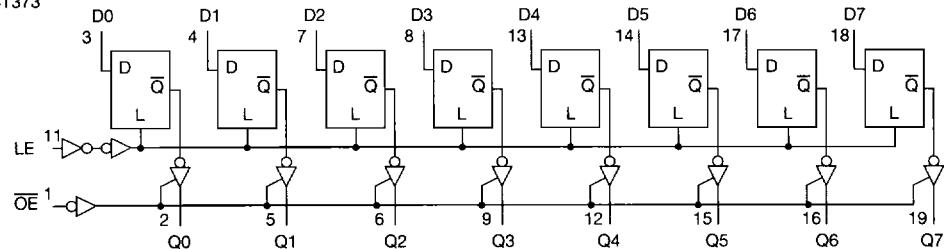
DC Electrical Characteristics

PARAMETER	SYMBOL	TEST CONDITION	V_{CC}	$T_a = 25^{\circ}\text{C}$			$T_a = -40\text{--}85^{\circ}\text{C}$		UNIT
				Min.	Typ.	Max.	Min.	Max.	
High-Level Input Voltage	V_{IH}	—	4.5~5.5	2.0	—	—	2.0	—	V
Low-Level Input Voltage	V_{IL}	—	4.5~5.5	—	—	0.8	—	0.8	V
High-Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50\mu\text{A}$	4.5	4.4	4.5	—	4.4	V
			$I_{OH} = -24\text{mA}$	4.5	3.94	—	—	3.80	
			$I_{OH} = -75\text{mA}^*$	5.5	—	—	—	3.85	
Low-Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50\mu\text{A}$	4.5	—	0.0	0.1	—	V
			$I_{OL} = 24\text{mA}$	4.5	—	—	0.36	—	
			$I_{OL} = 75\text{mA}^*$	5.5	—	—	—	1.65	
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	8.0	—	80.0	
			Per input: $V_{CC} = 3.4\text{V}$ Other input: V_{CC} or GND	5.5	—	—	1.35	—	1.5

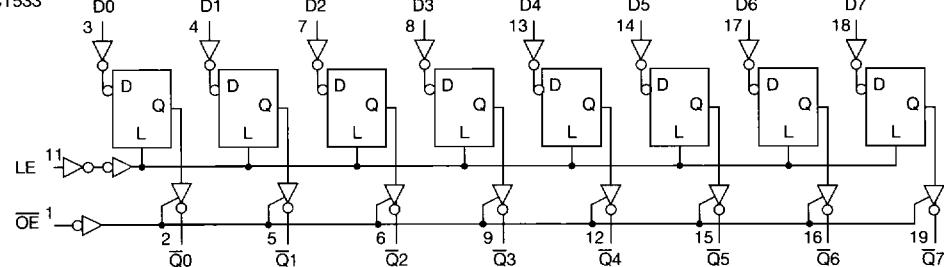
* This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

System Diagram

TC74ACT373



TC74ACT533

Timing Requirements (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40-85^\circ\text{C}$		UNIT
			V_{CC}	Typ.	Max.	Max.	Max.	
Minimum Pulse Width (LE)	$t_{W(H)}$	—	5.0±0.5	—	5.0	—	5.0	ns
Minimum Set-up Time	t_s	—	5.0±0.5	—	2.0	—	2.0	
Minimum Hold Time	t_h	—	5.0±0.5	—	3.0	—	3.0	

AC Electrical Characteristics ($C_L = 50\text{pF}$, $R_L = 500\Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40-85^\circ\text{C}$		UNIT	
			V_{CC}	Min.	Typ.	Max.	Min.		
Propagation Delay Time (LE-Q, \bar{Q})	t_{PLH} t_{PHL}	—	5.0±0.5	—	5.8	9.2	1.0	10.5	ns
Propagation Delay Time (Dn-Q, \bar{Q})	t_{PLH} t_{PHL}	—	5.0±0.5	—	5.9	9.6	1.0	11.0	
Output Enable Time	t_{PLZ} t_{PZH}	—	5.0±0.5	—	6.5	10.5	1.0	12.0	
Output Disable Time	t_{PLZ} t_{PZH}	—	5.0±0.5	—	5.5	7.8	1.0	9.0	pF
Input Capacitance	C_{IN}	—	—	—	5	10	—	10	
Output Capacitance	C_{OUT}	—	—	—	10	—	—	—	
Power Dissipation Capacitance	C_{PD}	—	—	—	32	—	—	—	

Note (1): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: $I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8$ (per Latch).

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation: $C_{PD(\text{total})} = 20 + 12 \cdot n$.